

# Improved Utilization of Photogenerated Charge Using Fluorine-Doped TiO<sub>2</sub> Hollow Spheres Scattering Layer in Dye-Sensitized Solar Cells

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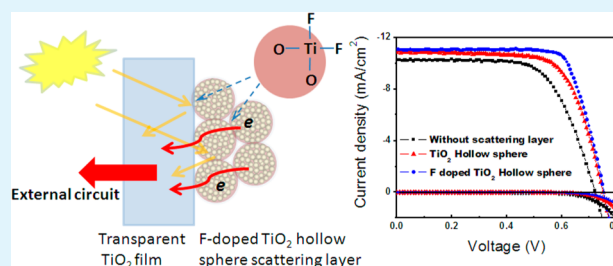
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**ABSTRACT:** We demonstrate a strategy to improve utilization of photogenerated charge in dye-sensitized solar cells (DSSCs) with fluorine-doped TiO<sub>2</sub> hollow spheres as the scattering layer, which improves the fill factor from 69.4% to 74.1% and in turn results in an overall efficiency of photoanode increased by 13% (from 5.62% to 6.31%) in comparison with the control device using undoped TiO<sub>2</sub> hollow spheres. It is proposed that the fluorine-doping improves the charge transfer and inhibition of charge recombination to enhance the utilization of the photogenerated charge in the photoanode.

**KEYWORDS:** dye-sensitized solar cells, scattering layer, electron transport, fluorine-doping, charge recombination, AC impedance



## 1. INTRODUCTION

Dye-sensitized solar cells (DSSCs) have attracted much attention because of their cost advantage in comparison with first generation solar cells.<sup>1–8</sup> In this type of solar cell, under illumination, the dye-absorbed semiconductor transports electron to the counter electrode accompanied with the hole eliminated by the redox reaction at the electrode/electrolyte interface. Therefore, rational design of the semiconducting electrode is crucial to improve the overall power conversion efficiency of devices.<sup>9–12</sup> Much effort has been devoted to increase the surface area or the thickness of photoanode for better light utility and thus higher photocurrent. However, unlimited increase of the electrode thickness is augmentation of a negative effect from an increased cell series resistance caused by an increased path-length between the electrons and the redox couple in the electrolyte. Various types of scattering layers such as photonic crystals and different metal oxide spheres<sup>13–18</sup> have been introduced to increase the absorption path-length of photons, create confinement property for enhancement of light harvesting, avoid the increment in series resistance, and enhance recombination probability.

However, the introduced transparent/light-scattering TiO<sub>2</sub> heterogeneous double layer architecture usually causes additional interfacial resistance between scattering layer and nanoporous TiO<sub>2</sub> film, leading to low utilization of photogenerated electrons in the scattering layer. In order to obtain better device performance, it is necessary to enhance the

electron transportation across the scattering layer to the nanoporous TiO<sub>2</sub> film, and then, the mesoporous TiO<sub>2</sub> can act as the light-scattering center as well as the electricity-generation source. Recently, studies have shown that an effective way to improve charge collection is by reducing the trap states<sup>19</sup> in semiconductor via heteroatom-doping.<sup>20–25</sup> According to our previous study, TiF<sub>4</sub> hydrolysis treatment of the photoanode could reduce the charge recombination and contact resistance.<sup>26</sup> Herein, we design a photoanode with fluorine-doped (F-doped) TiO<sub>2</sub> hollow nanoparticles coated on the top of the transparent TiO<sub>2</sub> nanoparticles layer to form the compact multifunctional photoanode. The electron and electrolyte transfer in this photoanode were studied by electrochemical impedance spectra (EIS). The results indicate that the F-doped hollow TiO<sub>2</sub> scattering layer significantly enhances the cell efficiency by decreasing the contact resistance between scattering layer and bottom transparent TiO<sub>2</sub> film.

## 2. EXPERIMENTAL SECTION

**2.1. Materials.** Titanium(IV) fluoride and hexadecylamine (HDA, 98%) were purchased from Sigma-Aldrich. Titanium(IV) *i*-propoxide (TTIP, 98%) was purchased from Stern Chemicals. Absolute ethanol (AR, Fisher Scientific), potassium chloride (AR, Fisher Scientific),

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ammonia solution (25 wt %, Fisher Scientific), and Milli-Q water (18.2 M $\Omega$  cm) were used for the synthesis.

**2.2. Preparation of TiO<sub>2</sub> Hollow Spheres and F-Doped TiO<sub>2</sub> Hollow Spheres.** Titanium(IV) *i*-propoxide (TTIP, 2.0 mmol), Titanium(IV) fluoride (0.4 mmol was added as F source for F-doped TiO<sub>2</sub> hollow spheres), and urea (4.0 mmol) were dissolved in 15 mL of ethanol. *tert*-Butyl ammonium hydroxide, 1.0 M solution in methanol (TBAH, 4.0 mmol, Sigma Aldrich), was added slowly into the solution. The mixture was stirred for 30 min to obtain a clear solution. Then, the mixture was processed by the hydrothermal method at 180 °C for 24 h. The white precipitate was cooled to room temperature, filtered, and washed several times with ethanol. The filtered white powdery titanium oxide was then sintered at 500 °C for 2 h in air.

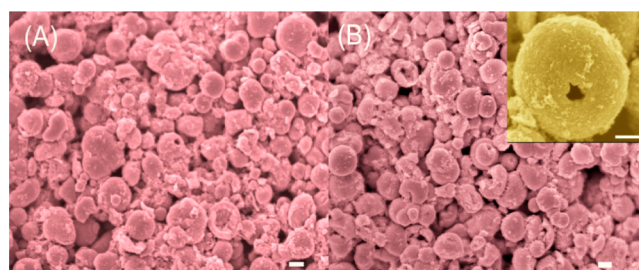
**2.3. Synthesis of Titanium Oxide and F-doped Titanium Oxide Hollow Sphere Gel.** Ethylcellulose 200 cPa (0.5 g) and ethanol (5.0 mL) were stirred to form a clear gel. Titanium oxide or F-doped titanium oxide hollow sphere (0.1 g) and terpineol (0.4 g) were then added into the mixture and stirred continually to form a homogeneous white gel.

**2.4. Preparation of Photoanode and Cell Assembly.** Briefly, transparent conducting glass (SnO<sub>2</sub>:F, FTO, 15  $\Omega$ /square, Solaronix) was cleaned in isopropyl alcohol and 0.1 M HCl solution using an ultrasonic bath for 30 min, respectively, and rinsed with water and ethanol. After treatment in a UV-ozone system (Model No. 256-220, Jelight Company) for 15 min, the FTO glass was immersed into 40 mM TiCl<sub>4</sub> solution at 70 °C for 30 min. Then, the 13.0  $\mu$ m thick TiO<sub>2</sub> (Ti-Nanoxide T/SP, Solaronix) electrodes were prepared by the doctor blading technique and gradually annealed under static air flow at 325 °C for 5 min, 375 °C for 5 min, 450 °C for 15 min, and 500 °C for 15 min according to the method as reported.<sup>2</sup> A TiO<sub>2</sub> scattering layer was coated on top of the transparent TiO<sub>2</sub> film and then treated by 40 mM TiCl<sub>4</sub> solution at 70 °C for another 30 min and sintered at 500 °C for 30 min. The electrodes were cooled to 80 °C and then immersed in 0.3 mM Z907 in acetonitrile/*tert*-butyl alcohol (1:1) for 10 h. Rinsed with acetonitrile, the photoanodes were bonded together with platinumized conducting glass (400 Å Pt fabricated by e-beam evaporation on the glass) using 60  $\mu$ m thermal-plastic Surlyn spacers. The areas of the electrodes were around 0.16 cm<sup>2</sup>. The ionic liquid electrolyte (EL-HPE) was introduced into the sandwich cells.

**2.5. Characterization of Samples.** The morphologies of TiO<sub>2</sub> spheres and films were studied by field emission scanning electron microscopy (FESEM, JEOL JSM-6360) and transmission electron microscopy (TEM, JEOL, JEM-1400). Powder X-ray diffraction (XRD) measurements were carried out using a Rikaku Rint-2000 instrument with Cu K $\alpha$  radiation. Nitrogen adsorption–desorption isotherms were obtained by ASAP 2020 (Micromeritics Instrument Corp.) apparatus. All the samples were degassed at 200 °C prior to Brunauer–Emmett–Teller (BET) measurements. The fluorine doping level of the sample was determined by X-ray photoelectron spectroscopy (XPS; KRATOS, AXIS ULTRA) using a monochromatized Al K $\alpha$  (1486.7 eV) X-ray source. The current–voltage characteristics of the cell under 100 mW cm<sup>-2</sup> (AM 1.5) conditions provided by Sun 2000 solar simulator (Abet-technologies, U.S.A.) were obtained by applying external potential bias to the cell, and the generated photocurrent was measured by a Keithley model 2440 digital source meter (Keithley, U.S.A.). The data was recorded using lab tracer software. The incident photon-to-current efficiency (IPCE) was obtained with Oriol QE/IPCE Kit equipment (Oriol, U.S.A.). Electrical impedance experiments were carried out in the dark and under illumination conditions with an autolab electrochemical workstation with a frequency range from 0.01 Hz to 0.1 MHz and a potential modulation of 20 mV. The forward bias is -0.69 V, and open-circuit voltage is in the dark and under illumination condition, respectively.

### 3. RESULTS AND DISCUSSION

The F doping effect on the HS morphology was first studied by SEM. As shown in Figure 1, the morphology of TiO<sub>2</sub> is not

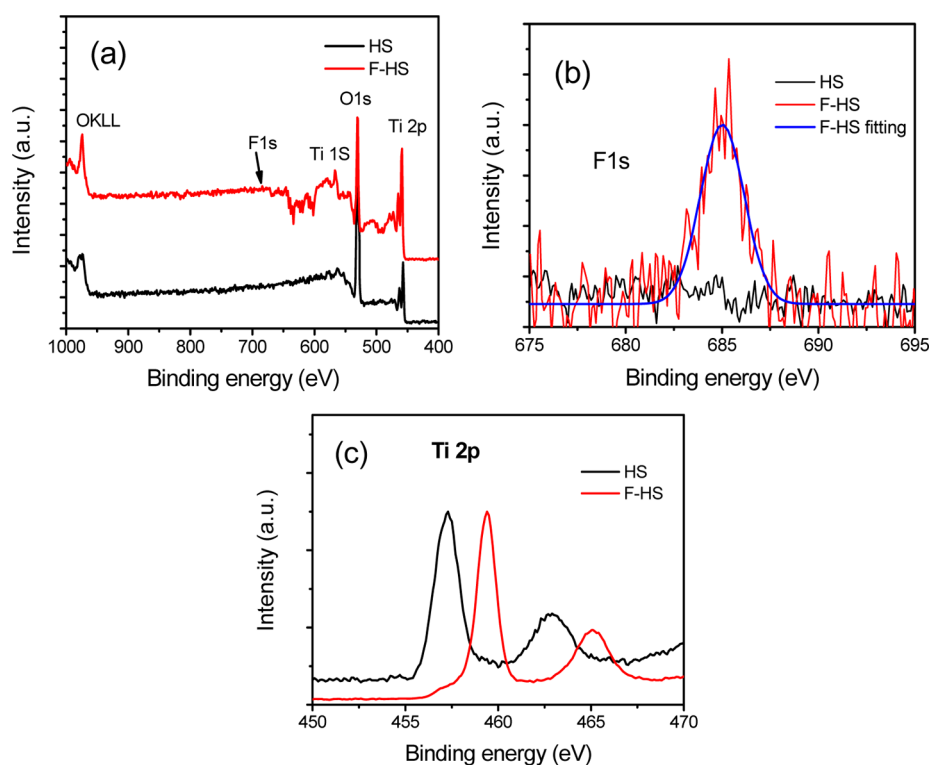


**Figure 1.** SEM images of undoped (a) and fluorine doped (b) TiO<sub>2</sub> hollow sphere (F-HS). Inset is the SEM image of single TiO<sub>2</sub> hollow sphere (F-HS). Scale bars in figures represent 1  $\mu$ m.

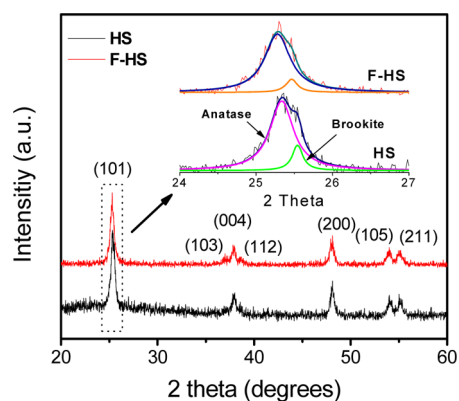
changed observably with F doping. The F-doped and undoped HS TiO<sub>2</sub> are composed of ca. 3  $\mu$ m spheres with fragmented parts. BET nitrogen gas adsorption technique was employed to determine the specific surface area of different TiO<sub>2</sub> structures. The HS and F-HS TiO<sub>2</sub> have nearly the same specific surface area and porosity, which are 77.1 m<sup>2</sup>/g and 70.0% for HS and 78.3 m<sup>2</sup>/g and 71.5% for F-HS TiO<sub>2</sub>, respectively. These results indicate the F doping does not significantly influence the morphology and specific surface area of TiO<sub>2</sub> hollow sphere; thus, it will not cause dramatic change on the dye loading ability and light scattering effect of HS.

The F doping state in TiO<sub>2</sub> HS structure was investigated by X-ray Photoelectron Spectroscopy (XPS). As shown in Figure 2a, besides the peaks at ~460 eV corresponding to the energies of the photoelectrons of Ti<sup>4+</sup>, the peaks at ~530 and 980 eV are attributed to the O 1s and O KLL, respectively.<sup>19,27,28</sup> A small peak at ~685 eV is observed in F-HS TiO<sub>2</sub> attributing to F1s. Figure 2b shows the high-resolution XPS spectra of F 1s region, beside a F 1s peak at 684.6 eV; no additional peaks are identified at higher energies. Therefore, the detected F should correspond to either F grafted on the surface of TiO<sub>2</sub> by substitution of the surface hydroxyl groups or physico-sorbed F.<sup>19,24</sup> The doping concentration of F estimated by XPS spectra is around 0.97 at%. The Ti 2p and O 1s in XPS spectra coming from Ti–O–Ti linkages in TiO<sub>2</sub> also showed significant changes upon Fluorine incorporation. Compared with the undoped HS (457.2 and 462.9 eV for Ti 2p<sub>3/2</sub> and Ti 2p<sub>1/2</sub>), the binding energy of Ti 2p<sub>3/2</sub> and Ti 2p<sub>1/2</sub> increased to 459.4 and 465.2 eV after fluorine-doping (as shown in Figure 4), indicating the different electronic interactions of Ti with anions, which causes partial electron transfer from Ti to F and a decrease in the electron density of Ti because of the lower electron negativity of fluorine compared to oxygen. Also, a decrease in the full width at half-maximum of the Ti 2p<sub>3/2</sub> peak from 1.52 to 1.18 eV is observed after F-HS TiO<sub>2</sub>. This peak narrowing phenomenon is related to the reduction in defect density of the HS TiO<sub>2</sub> by F-doping, which will be a benefit for electron transporting in TiO<sub>2</sub>.<sup>29</sup>

X-ray diffraction patterns of HS and F-HS TiO<sub>2</sub> are shown in Figure 3, which indicate that both HS and F-HS TiO<sub>2</sub> mainly contain anatase TiO<sub>2</sub> phase. The crystal size *D* of anatase phase of undoped and F-doped TiO<sub>2</sub> hollow sphere is estimated from the (101) peak according to the Scherrer equation,  $D = 0.89\lambda / \beta \cos\theta$ , where  $\lambda$ ,  $\beta$ , and  $\theta$  refer to X-ray wavelength (0.15418 nm), the half-maximum width, and the Bragg's angle, respectively. The calculated *D* is about 21.8 nm for HS and 19.9 nm for F-HS TiO<sub>2</sub>, respectively. As shown in inset of Figure 3, the F-doping reduces the percentage of brookite phase in TiO<sub>2</sub> hollow sphere, from 18.1% to 9.2%. This is due



**Figure 2.** XPS spectra of the undoped and F-doped TiO<sub>2</sub> hollow spheres (a). F 1s region (b) and high-resolution XPS of the Ti 2p (c).

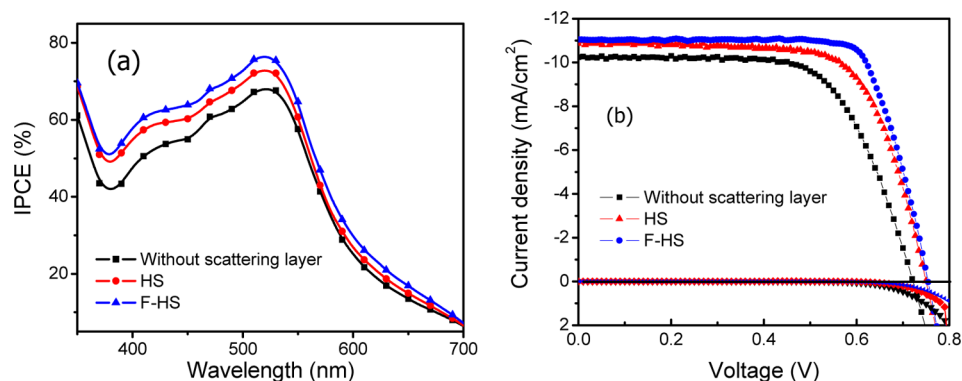


**Figure 3.** XRD patterns of HS and F-HS TiO<sub>2</sub> powder.

to the F<sup>-</sup> ions suppressing the crystallization of brookite by adsorbing onto the surfaces of TiO<sub>2</sub> particles.<sup>20</sup> A high

percentage of anatase phase would be a benefit for the DSSCs due to its higher charge transport ability.<sup>30</sup>

As discussed above, F-doping could reduce the defect density of TiO<sub>2</sub> hollow sphere and increase the percentage of anatase phase in TiO<sub>2</sub> hollow, which will be a benefit for charge transport in TiO<sub>2</sub> hollow structure. To investigate the F-doping of TiO<sub>2</sub> hollow sphere on the photovoltaic properties of the devices, the HS and F-HS TiO<sub>2</sub> scattering layers were formed on the transparent TiO<sub>2</sub> film (paste from Solaronix) to fabricate double layered photoelectrodes (devices 2 and 3, respectively), the control photoelectrode without scattering layer (device 1) also was fabricated for comparison. Figure 3a shows the incident photon-to-current efficiency (IPCE) curves of different photoelectrodes. The device 2 has higher IPCE values in the range of 350–550 nm than that of device 1, which is attributed to enhancement of light harvesting by Mie scattering effect and multiple reflections in the interior of the hollow structures.<sup>2,16–18</sup> It is noted that IPCE spectrum of device 3 is

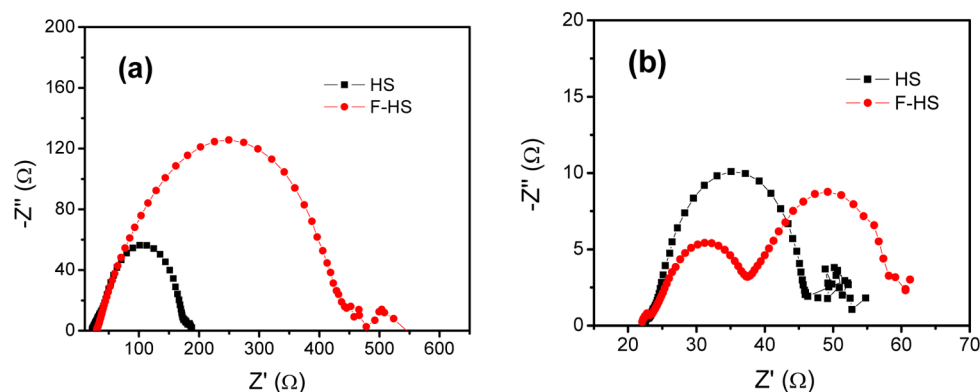


**Figure 4.** IPCE spectra of different photoelectrodes (a).  $J$ - $V$  characteristics of different photoelectrodes under AM 1.5 G 100 mW/cm<sup>2</sup> (b).

**Table 1. Performance Parameters of Photovoltaic Devices Based on Different TiO<sub>2</sub> Scattering Layer Photoelectrodes<sup>a</sup>**

devices	$J_{sc}$ (mAcm <sup>-2</sup> )	$V_{oc}$ (V)	FF (%)	$\eta$ (%)	adsorbed dye <sup>b</sup> (nmol·cm <sup>-2</sup> )	surface area (m <sup>2</sup> g <sup>-1</sup> )	porosity (%)
1	10.16	0.720	65.9	4.80	34.5	50 <sup>c</sup>	
2	10.80	0.750	69.4	5.62	38.0	77.1	70.0
3	11.00	0.754	76.1	6.31	39.0	78.3	71.5

<sup>a</sup>The active area of the photoelectrodes is 0.16 cm<sup>2</sup>. <sup>b</sup>The dye adsorbed on TiO<sub>2</sub> film was desorbed by a 0.1 M NaOH solution (water/ethanol 1:1 v/v) for 24 h. <sup>c</sup>BET data is obtained from Wuhan Geao Instruments Science and Technology Co. Ltd.

**Figure 5.** Nyquist plots of electrochemical impedance spectra of devices 2 and 3 in dark (a) and under illumination conditions (b).

quite similar to the device 2, just slightly higher than that in the whole response range of the device (350–700 nm), which indicates F-doping has no significant impact on the scattering effect of the hollow sphere and the light harvesting of photoelectrode, although the F-doped hollow sphere has smaller crystalline sizes and better crystallinity (as shown in the XRD results) that is reported to affect the visible-light absorption and light-scattering.<sup>31</sup> It could be explained that UV-light is not able to reach the scattering layer through the 13  $\mu\text{m}$  TiO<sub>2</sub> layer since the light penetration limit in TiO<sub>2</sub> is less than 1  $\mu\text{m}$ .

The photovoltaic properties ( $J$ – $V$  curves) of the devices were studied under AM 1.5 illumination (100 mW/cm<sup>2</sup>) (Figure 3b). The short-circuit current densities ( $J_{sc}$ ), open-circuit voltages ( $V_{oc}$ ), and fill factors (FF) of devices were summarized in Table 1. The overall conversion efficiency was obtained on the basis of the equation,  $\eta = J_{sc} \times V_{oc} \times \text{FF}/P_{in} \times 100\%$  where  $P_{in}$  is the incident radioactive flux. In comparison with the device 1 (without scattering layer), the overall conversion efficiency ( $\eta$ ) of device 2 (HS TiO<sub>2</sub> scattering layer) is increased by 17%, from 4.8% to 5.62%. The performance of photoelectrode is further enhanced by about 13% using F-HS TiO<sub>2</sub> hollow sphere as scattering layer resulting from the significantly enhanced fill factor (increased by  $\sim 10\%$ ) of devices, compared with the photoelectrode based on non F-doped TiO<sub>2</sub> hollow sphere, which reaches 6.31% with a  $J_{sc} = 11.0$  mA/cm<sup>2</sup>,  $V_{oc} = 0.754$  V, and FF = 76.1%. The  $J$ – $V$  characteristics in the dark were performed to obtain some evidence for the increased FF and  $J_{sc}$ . As shown in Figure 5, the dark current onset of F-HS TiO<sub>2</sub> device shifts to higher potential, in comparison with TiO<sub>2</sub>–HS device, and the dark-current of device 3 is smaller than that of device 2 at the same potential, indicating larger parallel resistance (recombination resistance) in F-HS device. Furthermore, the slope of  $J$ – $V$  curve near open-circuit voltage of F-HS device shows a slight increment, which is corresponding to the reduction of series resistance of DSSCs. On the basis of the  $J$ – $V$  curve and generalized Shockley equation used to study solar cell, FF of

DSSC is mainly decided by the recombination rate of electrons. Therefore, the significantly enhanced FF of devices can be attributed to the reduced charge recombination and enhanced charge transfer in a device with F-doped TiO<sub>2</sub> as scattering layer.<sup>32</sup> The beneficial effect of F doping on device performance can be explained by retarding the charge recombination through TiO<sub>2</sub> surface states by reducing oxygen vacancies via formation of the Ti–F bond and improving charge transport by a high percentage of anatase phase.

To further confirm the effects of F-doping on electron transport in the TiO<sub>2</sub> network and electron recombination between the injected electron and the redox electrolyte ( $\text{I}_3^-$ ), we carried out electrical impedance spectroscopy (EIS) measurements as shown in Figure 5. In the dark at  $-0.69$  V bias, no electrons were injected from dye sensitizer into TiO<sub>2</sub> network, electrons were just transported through the interconnected TiO<sub>2</sub> nanoparticles, after which they reacted with the redox electrolyte ( $\text{I}_3^-$ ). Thus, the charge-transfer resistance at the TiO<sub>2</sub>/dye/electrolyte interface ( $R_{ct}$ ) in the dark and under forward bias is related to the recombination process between the electrons at conducting band of TiO<sub>2</sub> nanoparticle and the electrolyte. This is estimated from the middle semicircle ( $1$ – $10^2$  Hz) in the Nyquist plots of EIS measured in the dark.<sup>33–40</sup> Parameters obtained from EIS are summarized in Table 2. The  $R_{ct}$  values of devices 2 and 3 are estimated to be 150.0 and 410.7  $\Omega$ , respectively. The

**Table 2. Recombination Resistance ( $R_{ct}$ ), Electron Transport Resistance ( $R_t$ ), Effective Electron Life Time ( $\tau$ ), and Electrolyte Diffusion Constant ( $D_{\text{I}_3^-}$ )**

devices	$R_{ct}$ ( $\Omega$ cm <sup>2</sup> )	$R_t$ ( $\Omega$ cm <sup>2</sup> )	$\tau$ (ms) <sup>a</sup>	$D_{\text{I}_3^-}$ ( $\times 10^{-6}$ cm <sup>2</sup> /s)
2	150	22.3	50.4	2.0
3	410.7	13.9	74.6	2.2

<sup>a</sup>Acquired by the inversion of frequency of the maximum imaginary impedance component at the medium frequency ( $1/2\pi f_{\text{max}}$ ) of the semicircle.

recombination resistance is nearly two times increased using F-HS as scattering layer. This means that F-HS device is better in retarding recombination between electrons at conducting band of TiO<sub>2</sub> nanoparticle and the electrolyte. Furthermore, the electron transport resistance ( $R_t$ ) was estimated from the Nyquist plots. Under the illumination and open circuit voltage condition,  $R_t$  is 22.3 and 13.9  $\Omega$  for devices 2 and 3, respectively, indicating faster electron transport in device 3 in comparison to that of device 2. Faster electron transport and low charge recombination rate in devices result in longer electron lifetime in devices in comparison to device 2 (50.4 and 74.6 ms for device 2 and 3, respectively). Therefore, from the analysis of EIS, the same conclusion as that from  $J$ - $V$  curves can be obtained, the F-doping reduced the trap states in TiO<sub>2</sub> surface, thus decreasing the charge transfer resistance and significantly increasing the recombination resistance between photoelectrode and electrolyte, resulting in a dramatic increase of FF and utilization of photogenerated electron.

In addition, the F-doping caused noteworthy change in the low frequency region of impedance spectra of devices. The semicircle in the low frequency ( $10^{-2}$ –1 Hz) region is related to the electrolyte diffusion and the impedance of electrolyte diffusion described by Nernst equation as follows,<sup>38,39</sup>  $Z_n = (W/(i\omega)^{1/2}) \tan h(((i\omega)/(K_N))^{1/2})$ , where  $W$  is the Warburg parameter  $W = ((kT)/(n^2 e_0^2 c_{i_3} A (D_{i_3})^{-1/2}))$  and  $K_N \delta^2 = D_{i_3}^-$ ;  $D_{i_3}^-$  is electrolyte diffusion constant,  $A$  is the electrode area,  $e_0$  is the elementary charge,  $k$  is Boltzmann constant,  $n$  is the number of electrons transported in each reaction (in general,  $n = 2$ ),  $T$  is the temperature,  $\delta$  is the thickness of Nernst diffusion layer, which is half of the distance between the electrodes).<sup>41–44</sup> The diffusion constant is  $2.0 \times 10^{-6}$  and  $2.2 \times 10^{-6}$  cm<sup>2</sup>/s for devices 2 and device 3, respectively. The analysis of EIS indicates that the use of F-doped TiO<sub>2</sub> as an active scattering layer can significantly improve current collection due to faster electron and electrolyte transport, resulting in significant enhancement in FF and PCE of DSSCs.

#### 4. CONCLUSION

In summary, we have investigated the photovoltaic properties of F-doping of TiO<sub>2</sub> hollow spheres in dye-sensitized solar cells. In comparison to the photoanode with the nondoped TiO<sub>2</sub> hollow spheres as the scattering layer, the overall conversion efficiency of the F-doped HS TiO<sub>2</sub> photoanode is increased by 13%. The use of F-doped TiO<sub>2</sub> hollow spheres as the active scattering layer can significantly improve current collection due to faster electron, higher electrolyte diffusion ability, and reduced electron loss from the grain boundary scattering and low recombination at the TiO<sub>2</sub>/electrolyte interface. It is worthy of note that a better DSSC efficiency can be achieved by fabrication of the thickness of TiO<sub>2</sub> photoanode equal or close to the electron diffusion length. If the thickness of TiO<sub>2</sub> photoanode (bottom transparent TiO<sub>2</sub> film + scattering layer) in this work is not optimized, it is possible to further improve the device performance and is planned to be conducted. This work demonstrates a multifunctional scattering layer and provides a promising strategy to explore high-efficiency DSSCs.

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#### Author Contributions

#These authors contributed equally to this work.

#### Notes

The authors declare no competing financial interest.

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